

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	10	(("6165873") or ("6057243") or ("6165880") or ("6204161") or ("5902132") or ("6017784") or ("6072241") or ("6071799") or ("6078073") or ("6080648")).PN.	USPAT; US-PGPUB	2002/12/02 09:05
2	IS&R	38	(("6083816") or ("6091154") or ("6140673") or ("6156636") or ("6180472") or ("6200855") or ("6211047") or ("6218235") or ("6211047") or ("6218235") or ("6235627") or ("6245621") or ("6248654") or ("6251721") or ("6287905") or ("6287914") or ("6299314") or ("6333233") or ("6344692") or ("6352931") or ("6369423") or ("6372575") or ("6376386") or ("6444559") or ("6468857") or ("6271573") or ("6316349") or ("6337273") or ("6436775") or ("6069038") or ("5683922") or ("6207486") or ("6274425") or ("6284596") or ("6337262") or ("6417046") or ("6432816") or ("6448179") or ("6103572") or ("5334860")).PN.	USPAT; US-PGPUB	2002/12/02 09:05
3	BRS	19	("3928095" "4994410" "4997790" "5106783" "5206187" "5208472" "5364804" "5378654" "5439846" "5578524" "5587338" "5668052" "5719071" "5786276" "5817562" "5897372" "5902132" "5914542" "5926794").PN.	USPAT	2002/12/02 09:09
4	BRS	9	("5304509" "5543648" "5744401" "5773354" "5876497" "6008110").PN.	USPAT	2002/12/02 09:10
5	BRS	24	("4900257" "5164333" "5168072" "5232850" "5258645" "5304829" "5317180" "5378910" "5397909" "5401666" "5438006" "5506440" "5517045" "5523616" "5567638" "5578524" "5585304" "5616933" "5631484" "5828130" "5877081" "5894160" "6018184" "6057604").PN.	USPAT	2002/12/02 09:11
6	BRS	7	("5036370" "5061985" "5302551" "5573965" "5612254" "5661344" "5682209").PN.	USPAT	2002/12/02 09:12
7	BRS	4	("5682209" "6008084" "6022776" "6037215").PN.	USPAT	2002/12/02 09:14
8	IS&R	302	(257/311,535).CCLS.	USPAT; US-PGPUB	2002/12/02 09:45
9	IS&R	30	(257/311,535).CCLS.	EPO; JPO; DERWENT	2002/12/02 09:45
10	BRS	4	("5981369" "6258649" "6291289" "6215144").PN.	USPAT	2002/12/02 10:39
11	IS&R	1	("6150689").PN.	USPAT; US-PGPUB	2002/12/02 10:44
12	BRS	10	("4937645" "5188975" "5204286" "5264712" "5336638" "5471079" "5760475" "5783471" "5793076" "5796166").PN.	USPAT	2002/12/02 10:44
13	BRS	4	jp-07106437-\$.did. or jp-06053494-\$.did.	EPO; JPO; DERWENT	2002/12/02 12:31

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 6461911 B2 24		Semiconductor memory device and fabricating method thereof	438/253	257/298; 257/308; 257/311; 438/241; 438/396	Ahn, Tae-hyuk et al.
2	US 6433381 B1 46		Semiconductor device and method of manufacturing the same	257/311	257/296; 257/306	Mizutani, Kazuhiro et al.
3	US 6399974 B1 18		Semiconductor memory device using an insulator film for the capacitor of the memory cell and method for manufacturing the same	257/296	257/298; 257/306; 257/307; 257/310; 257/311; 257/532	Ohtsuki, Sumito
4	US 6333538 B1 23		COB DRAM having contact extending over element-isolating film	257/311	257/306	Hosotani, Keiji et al.
5	US 6326315 B1 15		Low temperature rapid ramping anneal method for fabricating layered superlattice materials and making electronic devices including same	438/758	257/296; 257/300; 257/311; 257/532; 438/239; 438/256; 438/3; 438/386; 438/399	Uchiyama, Kiyoshi et al.
6	US 6316803 B1 32		Integrated circuit memory devices having self-aligned contact	257/311	257/300; 257/306	Ban, Hyo-dong et al.
7	US 6232628 B1 11		Semiconductor device having stacked capacitor structure	257/306	257/296; 257/298; 257/301; 257/303; 257/304; 257/309; 257/311; 257/317; 438/253; 438/255; 438/260; 438/396	Shirosaki, Masami et al.
8	US 6222223 B1 77		Semiconductor device including capacitance element having high area efficiency	257/311	257/306; 257/532; 257/E27.084; 438/253; 438/396	Tobita, Youichi

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
9	US 6169304 B1	25	Semiconductor device having a passivation layer which minimizes diffusion of hydrogen into a dielectric layer	257/295	257/296; 257/532; 257/535; 257/640; 257/649; 257/E27.104	Arita, Koji et al
10	US 6160284 A	44	Semiconductor device with sidewall insulating layers in the capacitor contact hole	257/306	257/311; 438/253; 438/396	Hachisuka, Atsushi et al.
11	US 6150689 A	73	Semiconductor integrated circuit device and method for manufacturing the same	257/306	257/311; 257/412; 257/413; 257/915	Narui, Seiji et al
12	US 5936272 A	15	DRAM transistor cells with a self-aligned storage electrode contact	257/306	257/308; 257/311; 257/E27.089	Lee, Kyu-pil
13	US 5604696 A	42	Stacked capacitor type semiconductor memory device with good flatness characteristics	365/149	257/303; 257/304; 257/311; 257/E27.089	Takaishi, Yoshihiro
14	US 5561311 A	18	Semiconductor memory with insulation film embedded in groove formed on substrate	257/309	257/306; 257/308; 257/311; 257/905; 257/908; 257/E27.086	Hamamoto, Takeshi et al.
15	US 5432732 A	34	Dynamic semiconductor memory	365/149	257/296; 257/301; 257/304; 257/310; 257/311; 257/E27.085; 438/253; 438/396	Ohmi, Tadahiyo
16	JP 06169068 A	6	SEMICONDUCTOR MEMORY CELL AND ITS MANUFACTURE		257/296; 257/311	TSURU, MASAHIRO

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/050.169 on November 04, 2002

Combined Classifications

7 438/241
5 438/253
5 438/396
5 438/595
4 257/758
4 438/258
4 438/303
4 438/592
4 438/597
4 438/618
4 438/624
3 257/296
3 438/197
3 438/257
3 438/587
3 438/637
3 438/672
3 438/738
2 257/301
2 257/306
2 257/750
2 257/770
2 438/239
2 438/256
2 438/261
2 438/263
2 438/265
2 438/279
2 438/284
2 438/299
2 438/301
2 438/533
2 438/585
2 438/586
2 438/612
2 438/620
2 438/639
2 438/656
2 438/666
2 438/671
2 438/675
2 438/700
2 438/702
2 438/706
2 438/714
2 438/715
2 438/787

	Document ID	Pages	Title	Current OR	Current XRef	Inventor	Issue Date
1	US 6344692 B1	51	Highly integrated and reliable DRAM adapted for self-aligned contact	257/758	257/296; 438/622; 438/791	Ikemasu, Shinichiroh et al.	20020205
2	US 5587338 A	9	Polysilicon contact stud process	438/672	438/664; 438/705	Tseng, Horng-Huei	19961224
3	US 5661344 A	8	Porous dielectric material with a passivation layer for electronics applications	257/758	257/637; 257/642; 257/759; 257/760	Havemann, Robert H. et al.	19970826
4	US 5612254 A	15	Methods of forming an interconnect on a semiconductor substrate	438/634	438/631; 438/637; 438/672; 438/675	Mu, Xiao-Chun et al.	19970318
5	US 6037215 A	14	Fabricating methods including capacitors on capping layer	438/253		Lee, Joo-young et al.	20000314

Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/050,169 on November 04, 2002

7 438/241 (5 OR, 2 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS

438/197 Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)

438/238 Including passive device (e.g., resistor,
capacitor, etc.)

438/239 Capacitor

438/241 And additional field effect transistor
(e.g., sense or access transistor, etc.)

5 438/253 (1 OR, 4 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS

438/197 Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)

438/238 Including passive device (e.g., resistor,
capacitor, etc.)

438/239 Capacitor

438/253 Stacked capacitor

5 438/396 (0 OR, 5 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/381 MAKING PASSIVE DEVICE (E.G., RESISTOR,
CAPACITOR, ETC.)

438/396 Stacked capacitor

5 438/595 (1 OR, 4 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/584 COATING WITH ELECTRICALLY OR THERMALLY
CONDUCTIVE MATERIAL

438/585 Insulated gate formation

438/595 Having sidewall structure

4 257/758 (1 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/734 (E) COMBINED WITH ELECTRICAL CONTACT OR LEAD

257/741 (E) Of specified material other than unalloyed
aluminum

257/750 (E) Layered

257/758 Multiple metal levels on semiconductor,
separated by insulating layer (e.g., multiple level
metallization for integrated circuit)

PLUS Search Results for S/N 10/050.169. Searched November 04, 2002 (Top 50)

6165873	6083816	6235627	6369423	5683922
6057243	6091154	6245621	6372575	6207486
6165880	6140673	6248654	6376386	6274425
6204161	6156636	6251721	6444559	6284596
5902132	6180472	6287905	6468857	6337262
6017784	6200855	6287914	6271573	6417046
6072241	6211047	6299314	6316349	6432816
6071799	6218235	6333233	6337273	6448179
6078073	6211047	6344692	6436775	6103572
6080648	6218235	6352931	6069038	5334860